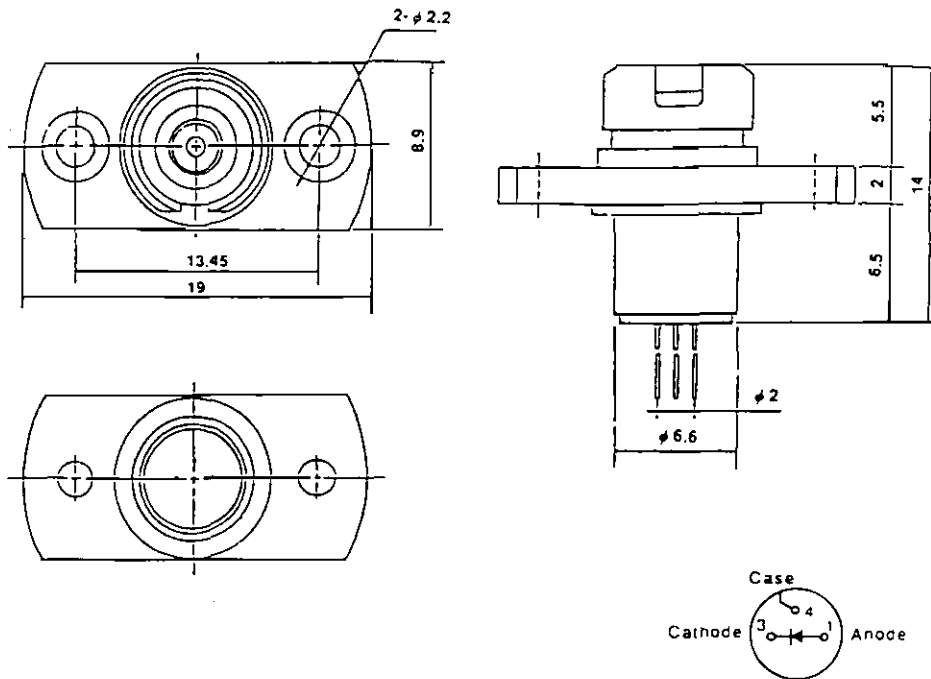


PHOTO DIODE NDL5561RC

1000 to 1600nm OPTICAL FIBER COMMUNICATIONS
InGaAs AVALANCHE PHOTO DIODE RECEPTACLE MODULE

PACKAGE DIMENSIONS in millimeters



The information in this document is subject to change without notice.

ABSOLUTE MAXIMUM RATINGS(Tc=25°C)

Forward Current	IF	10	mA
Reverse Current	IR	0.5	mA
Operating Temperature	Top	-40 to +70	°C
Storage Temperature	Tstg	-40 to +85	°C
Lead Soldering Temperature(10sec)	Ts	260	°C

ELECTRO-OPTICAL CHARACTERISTICS(Tc=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Reverse Breakdown Voltage	V(BR)R	50	75	100	V	ID=100 μA
Temperature Coefficient of Reverse Breakdown Voltage	δ		0.2		%/°C	
Dark Current	ID		8	30	nA	VR=0.9VBR
Multiplied Dark Current	IDM		0.2	2	nA	M=2~10
Terminal Capacitance	Cr		0.8	2	pF	VR=0.9VBR
Cut-off Frequency	fc	700			GHz	M=10
Quantum Efficiency	η	70	85		%	λ = 1300nm
			80			λ = 1550nm
Sensitivity	S	0.73	0.89		A/W	λ = 1300nm
			1.0			λ = 1550nm
Multiplication Factor	M	20	40			Ipo=1 μA, λ = 1550nm, VR=V(@ID=1 μA)
Excess Noise Factor	x		0.7			
Excess Noise Coefficient	F		5			λ = 1300,1550nm, Ipo=1 μA, M=10, f=35MHz, B=1MHz